

a second step of growing a semiconductor layer of nitride on said raised and recessed region in said upper portion of said base substrate so that a recessed portion in said raised and recessed region is filled and the upper surface thereof is even; and

a third step of irradiating an interface between said semiconductor layer and said base substrate with a laser beam, thereby separating said semiconductor layer from said base substrate to form a semiconductor substrate from said semiconductor layer,

wherein in said third step, the laser beam is irradiated upon said semiconductor layer from the surface opposite to the upper portion of said base substrate.

### **REMARKS**

The Examiner's final Office Action of November 18, 2002 has been received and its contents carefully noted. Applicant would like to thank the Examiner for indicating the allowance of claims 3-8. Applicant respectfully submits that this response is timely filed and fully responsive to the final Office Action.

Claims 1-8 were pending in this application prior to the aforementioned amendment, with claims 3-8 being indicated as allowed over the prior art of record. By the above actions, claim 1 has been amended to provide a third irradiation step similar to allowed claim 8 which is fully supported by the specification, pages 13 and 14, as well as Figure 4. That is, claim 1 now recites the added limitation that:

“wherein in said third step, the laser beam is irradiated upon said semiconductor layer from the surface opposite to the upper portion of said base substrate.”

Accordingly, claims 1-8 remain pending in this application, and are believed to be in condition for allowance for at least the reasons stated below.

### **35 U.S.C. §103 Rejection**

Claim 1 stands rejected under 35 U.S.C. §103(a) as unpatentable over Asai et al ('519) in view of the teachings of Cook ('078). Asai et al (Figures 4 and 5) discloses a